



IRF840

N - CHANNEL 500V - 0.75Ω - 8A - TO-220 PowerMESH™ MOSFET

TYPE	V _{DSS}	R _{DS(on)}	I _D
IRF840	500 V	< 0.85 Ω	8 A

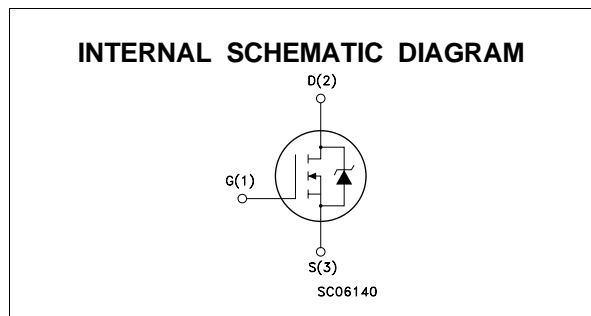
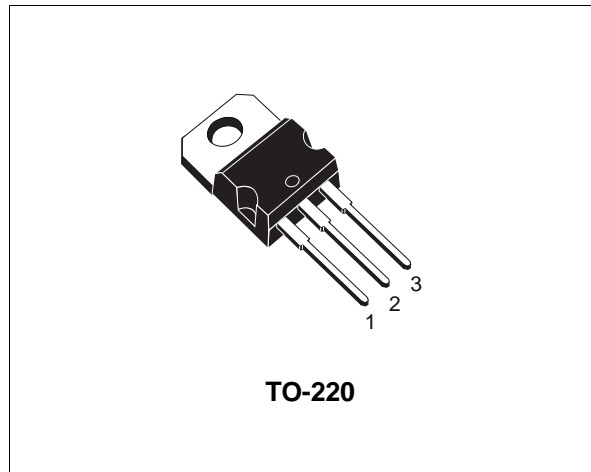
- TYPICAL R_{DS(on)} = 0.75 Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- VERY LOW INTRINSIC CAPACITANCES
- GATE CHARGE MINIMIZED

DESCRIPTION

This power MOSFET is designed using the company's consolidated strip layout-based MESH OVERLAY™ process. This technology matches and improves the performances compared with standard parts from various sources.

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLIES (SMPS)
- DC-AC CONVERTERS FOR WELDING EQUIPMENT AND UNINTERRUPTIBLE POWER SUPPLIES AND MOTOR DRIVER



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	500	V
V _{DGR}	Drain- gate Voltage (R _{GS} = 20 kΩ)	500	V
V _{GS}	Gate-source Voltage	± 20	V
I _D	Drain Current (continuous) at T _c = 25 °C	8.0	A
I _D	Drain Current (continuous) at T _c = 100 °C	5.1	A
I _{DM} (●)	Drain Current (pulsed)	32	A
P _{tot}	Total Dissipation at T _c = 25 °C	125	W
	Derating Factor	1.0	W/°C
dv/dt(1)	Peak Diode Recovery voltage slope	3.5	V/ns
T _{stg}	Storage Temperature	-65 to 150	°C
T _j	Max. Operating Junction Temperature	150	°C

(●) Pulse width limited by safe operating area

(1) I_{SD} ≤ 8A, di/dt ≤ 100 A/μs, V_{DD} ≤ V_{(BR)DSS}, T_j ≤ T_{JMAX}

First Digit of the Datecode Being Z or K Identifies Silicon Characterized in this Datasheet

IRF840

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	1.0	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	62.5	°C/W
R _{thc-sink}	Thermal Resistance Case-sink	Typ	0.5	°C/W
T _l	Maximum Lead Temperature For Soldering Purpose		300	°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max)	8.0	A
E _{AS}	Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 50 V)	520	mJ

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 μA V _{GS} = 0	500			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating T _c = 125 °C			1 50	μA μA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 20 V			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} I _D = 250 μA	2	3	4	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10V I _D = 4.8 A		0.75	0.85	Ω
I _{D(on)}	On State Drain Current	V _{DS} > I _{D(on)} × R _{DS(on)max} V _{GS} = 10 V	8.0			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (*)	Forward Transconductance	V _{DS} > I _{D(on)} × R _{DS(on)max} I _D = 4.8 A	4.9			S
C _{iss} C _{oss} C _{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V _{DS} = 25 V f = 1 MHz V _{GS} = 0		1300 200 18		pF pF pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Time	$V_{DD} = 250\text{ V}$ $I_D = 4.3\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 3)		19		ns
t_r	Rise Time			11		ns
Q_g	Total Gate Charge	$V_{DD} = 400\text{ V}$ $I_D = 8.0\text{ A}$ $V_{GS} = 10\text{ V}$		39	50	nC
Q_{gs}	Gate-Source Charge			10.6		nC
Q_{gd}	Gate-Drain Charge			13.7		nC

SWITCHING OFF

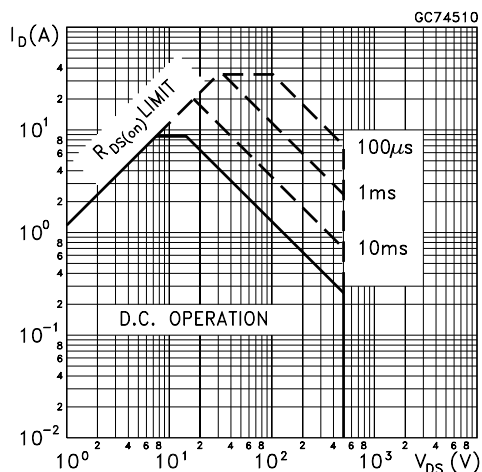
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{DD} = 400\text{ V}$ $I_D = 8\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 5)		11.5		ns
t_f	Fall Time			11		ns
t_c	Cross-over Time			20		ns

SOURCE DRAIN DIODE

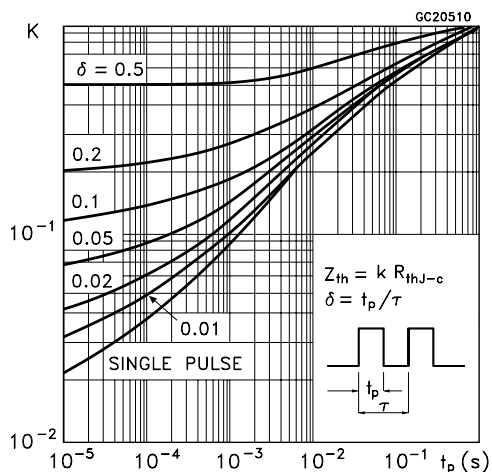
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				8.0	A
$I_{SDM}(\bullet)$	Source-drain Current (pulsed)				32	A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 8.0\text{ A}$ $V_{GS} = 0$			1.6	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 8.0\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$ (see test circuit, figure 5)		420		ns
Q_{rr}	Reverse Recovery Charge			3.5		μC
I_{RRM}	Reverse Recovery Current			16.5		A

(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %
 (•) Pulse width limited by safe operating area

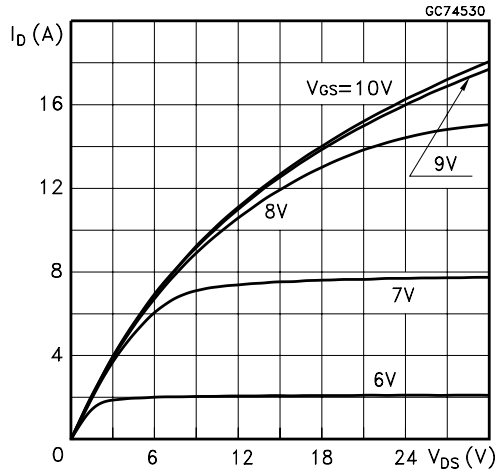
Safe Operating Area



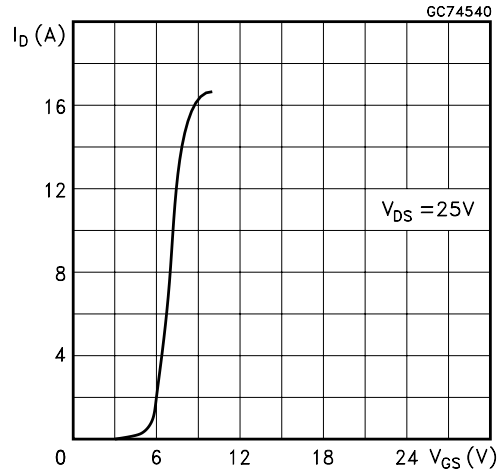
Thermal Impedance



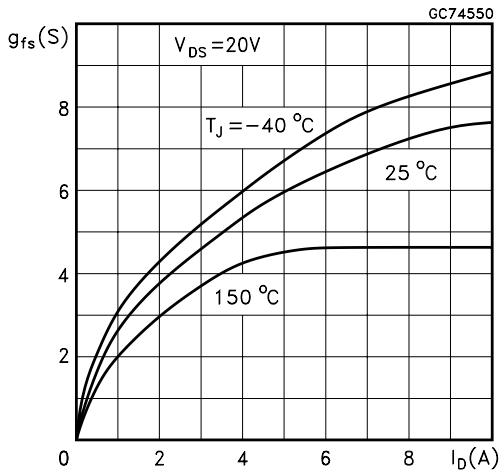
Output Characteristics



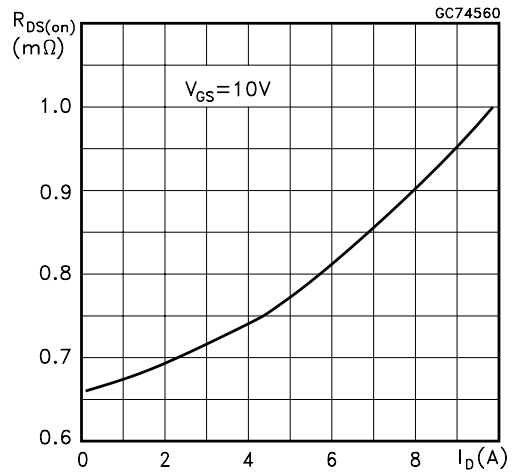
Transfer Characteristics



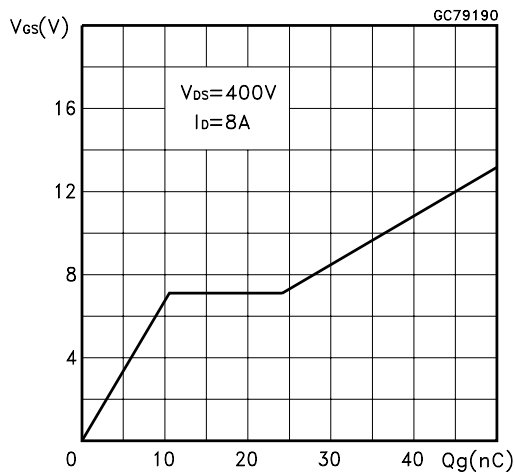
Transconductance



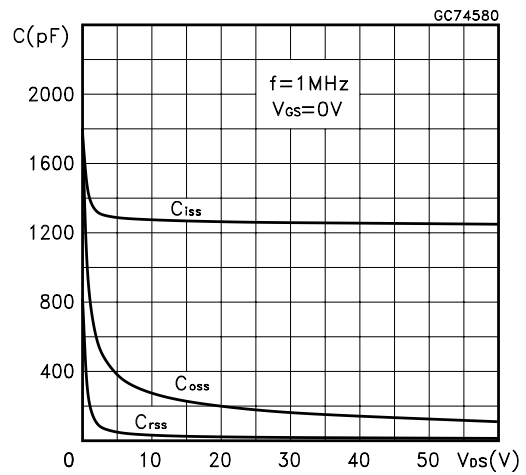
Static Drain-source On Resistance



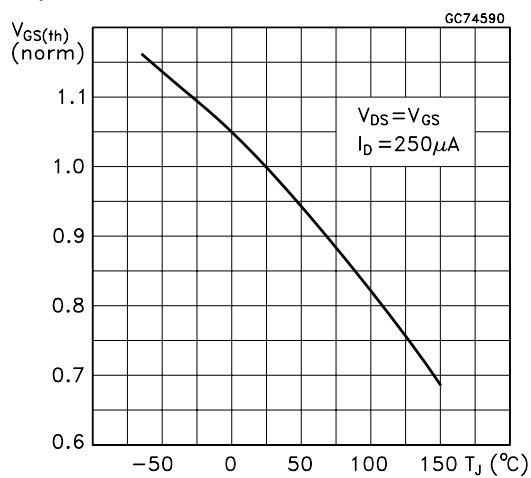
Gate Charge vs Gate-source Voltage



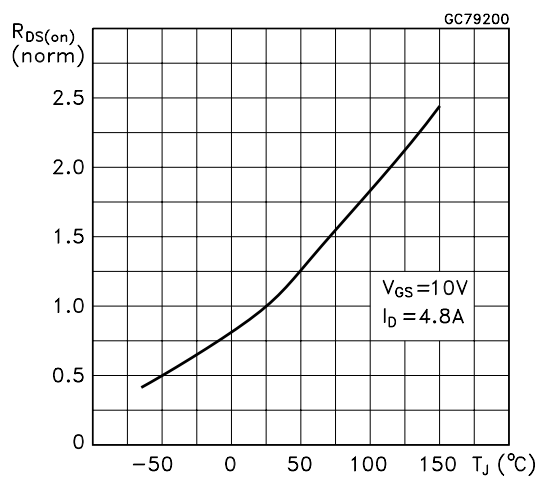
Capacitance Variations



Normalized Gate Threshold Voltage vs Temperature



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

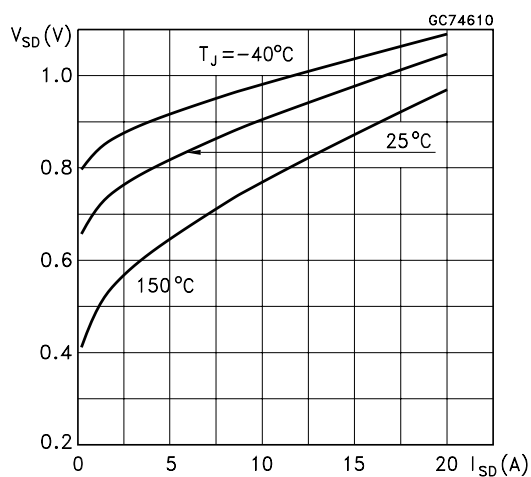


Fig. 1: Unclamped Inductive Load Test Circuit

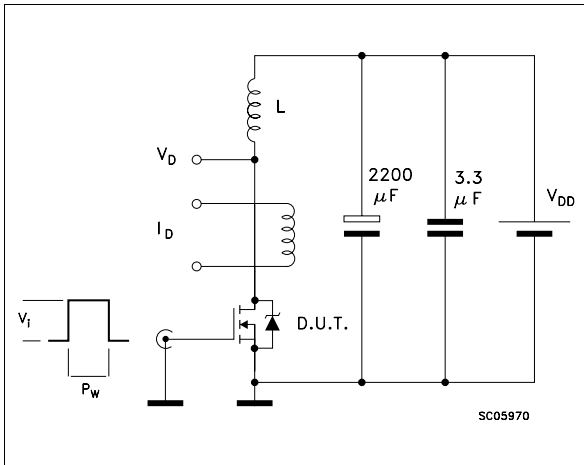


Fig. 1: Unclamped Inductive Waveform

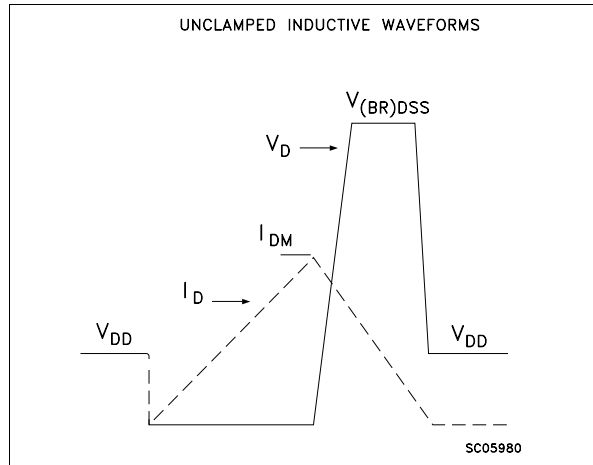


Fig. 3: Switching Times Test Circuits For Resistive Load

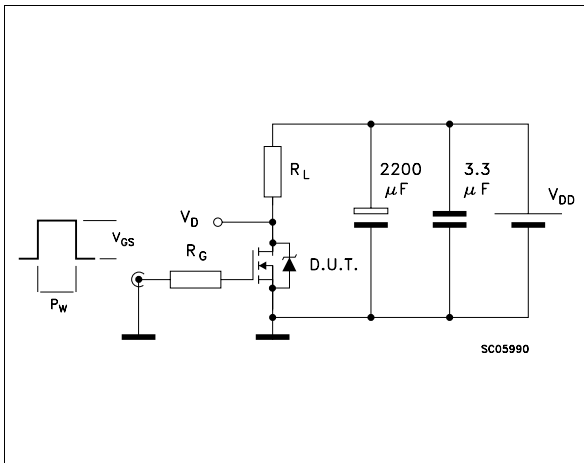


Fig. 4: Gate Charge test Circuit

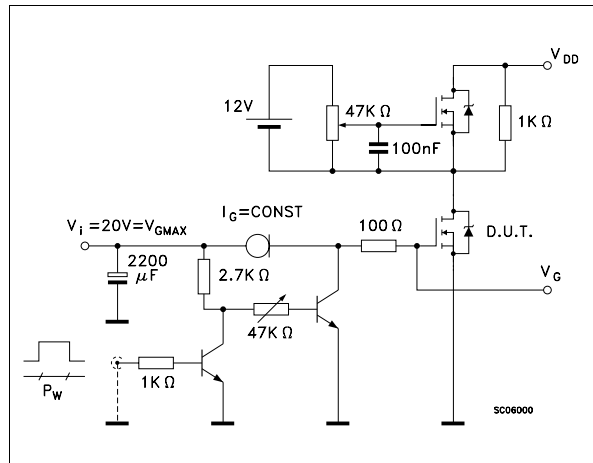
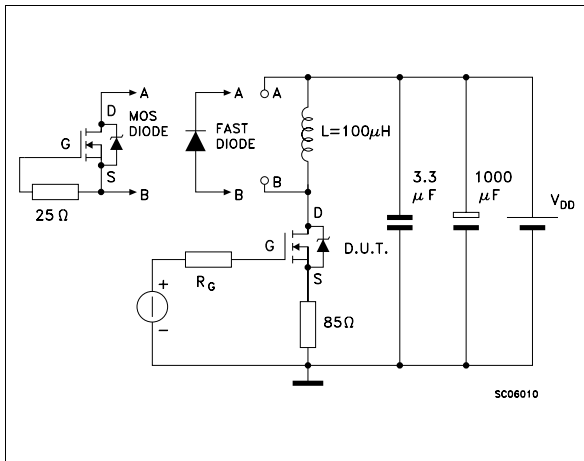
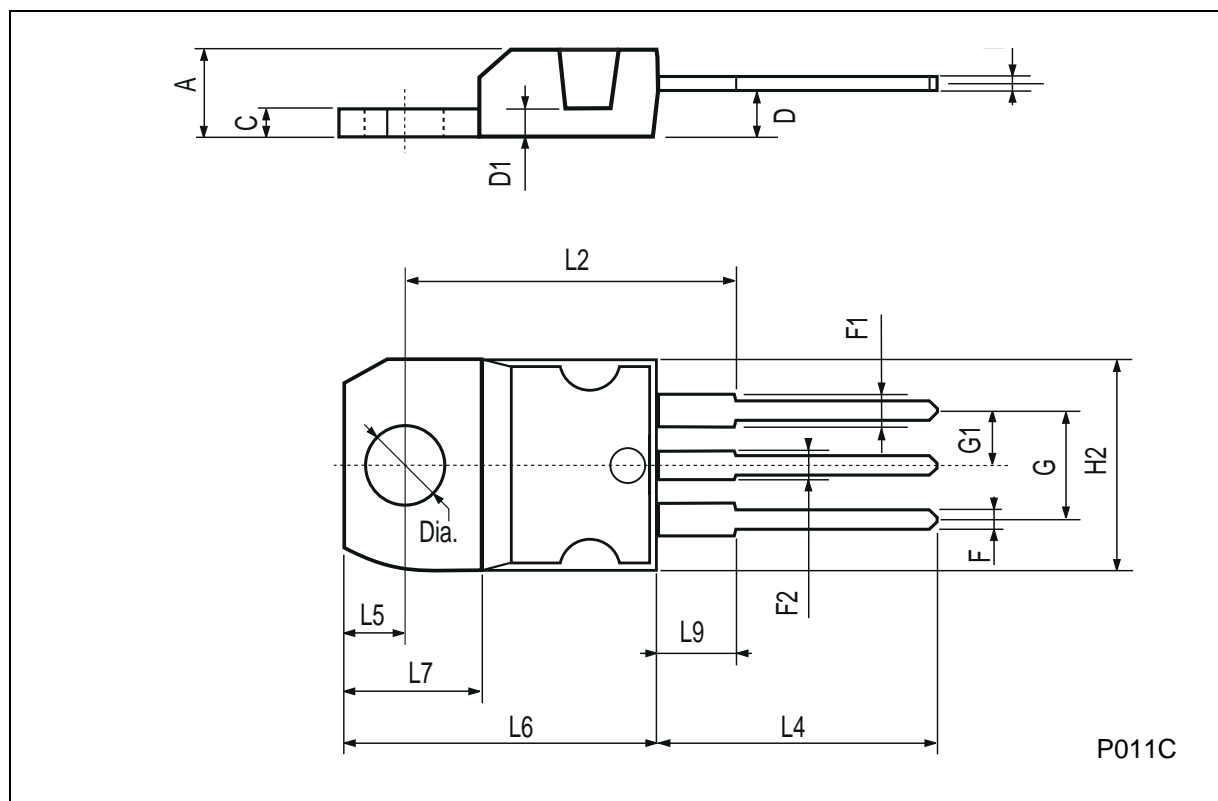


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



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